

a substrate support for a substrate to be processed, located inside the plasma generation chamber;

an endless annular wave guide with a plurality of slots for radiating microwaves therethrough provided outside of said first dielectric material;

gas inputs situated to introduce gas into said plasma generation chamber;

an evacuation system situated to permit pressure reduction in said plasma generation chamber;

wherein an interior of said wave guide is filled with a second dielectric material which is the same as or different from said first dielectric material so that the wavelength of microwaves in said wave guide is shortened.

---

78. (Twice Amended) A microwave plasma processing method wherein a substrate is placed in a microwave plasma processing apparatus comprising a plasma generation chamber provided with a first dielectric material; means for supporting a substrate to be processed; microwave introduction means utilizing an endless annular wave guide provided outside of said plasma generation chamber and provided with plural slots for irradiating microwaves therethrough; means for introducing gas for said plasma generation chamber; and evacuation means for said plasma generation chamber, wherein the interior of said wave guide is filled with a second dielectric material which is the same as or different from the first dielectric material, so that the wavelength of microwaves in said wave guide is shortened, thereby effecting a plasma process.

---